

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	(non near vibrat\$4 with difference with potential and chemical and sample).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/09/12 08:39
S1	1	nvcpd near sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:15
S2	1	nvcpd	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:15
S3	2	scan\$4 same wafer same sensor same voltage same vibrat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:16
S4	85	scan\$4 same wafer same sensor same voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:22
S5	57	vibrat\$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:22
S6	21	vibrat\$3 with contact with potential with difference and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:20
S7	5	non near vibrat\$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:04
S8	6	non near vibrat\$3 with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:05
S9	1	vibrat\$3 with contact with potential with difference and semiconductor and defect and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:08
S10	2	vibrat\$3 with contact with potential with difference and semiconductor and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:09

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S11	12	vibrat\$3 with contact with potential with difference and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:07
S12	1	1991-213740.NRAN.	DERWENT	OR	OFF	2004/09/07 13:20
S13	7	defect same semiconductor and contact same potential same difference same sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:42
S14	7	defect same semiconductor and contact same potential same difference same vibrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:45
S15	0	defect same semiconductor and Kelvin same (non near vibrat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:46
S16	11	defect same semiconductor and Kelvin same vibrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:46
S17	4	category with defect with chemical	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 10:59
S18	9	category with defect with electronic	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 10:53
S19	71	treat with defect with improv\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:00
S20	6	treat with defect with improv\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:01
S21	99	treat\$3 with defect with improv\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:02
S22	329	treat\$5 with defect with improv\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:02

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S23	6	(analyz\$3 analysis) with chemical with contaminant with auger	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:08
S24	119	take.inv. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/23 12:23
S25	1	wafer near handler and remed\$4 with defect and clean\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:30
S26	1	wafer near handler and remed\$4 with defect and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:30
S27	39	wafer near handler and clean\$3 with defect and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:32
S28	25	wafer near handler and clean\$3 with defect and semiconductor and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:35
S29	27	wafer near handler and clean\$3 same defect and semiconductor and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:41
S30	518	sensors! same clean\$3 same (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:42
S31	36	sensors! same clean\$3 same (semiconductor wafer) same handl\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:43
S32	13	438/906.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:11
S33	26	438/906.ccls. and sensors	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:12
S34	9	438/12.ccls. and sensors	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:12

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S35	6	438/12.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:14
S36	18	438/12.ccls. and clean\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:20
S37	6	438/12.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:21
S38	3	sensors! same clean\$3 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:23
S39	14	sensors same clean\$3 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:03
S40	0	sensors same remed\$4 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:02
S41	96	sensors same clean\$3 same semiconductor and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:03
S42	3	sensors same clean\$3 same semiconductor same monitor\$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:05
S43	64	134/1.3.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:16
S44	24	134/1.2.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:16
S45	269	transport\$3 same clean same (semiconductor wafer) same handl\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:34
S46	0	transport\$3 same clean same (semiconductor wafer) same handl\$3 same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:34

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S47	71	transport\$3 same clean same (semiconductor wafer) same handl\$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:36
S48	0	transport\$3 same clean\$4 same (semiconductor wafer) same handl\$3 same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:37
S49	111	transport\$3 same clean\$4 same (semiconductor wafer) same handl\$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:50
S50	46	transport\$3 same defect same (semiconductor wafer) same handl\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:02
S51	31	monitor\$3 with clean\$3 same (semiconductor wafer) same sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:17
S52	7	determin\$3 same cleanliness same wafer same improv\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:20
S53	7	determin\$3 same cleanliness same semiconductor same improv\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:21
S54	594	modify\$3 same clean\$3 same improv\$	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:21
S55	36	modify\$3 same clean\$3 same improv\$ same (wafer semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:22
S56	28	decompos\$3 with signal with wavelet with domain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:43
S57	6	decompos\$3 with signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S58	118	signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52

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S59	87	signal with wavelet with domain and coefficient and peak and \$2compos\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:42
S60	6	\$2compos\$3 with signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S61	32	signal with wavelet with domain and coefficient and peak and \$2compos\$3 and revers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:53
S62	13	signal with wavelet with domain and coefficient and peak and revers\$3 near order	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:57
S63	30	signal with wavelet with domain and coefficient and peak and revers\$3 and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:48
S64	8	signal with wavelet with domain and coefficient and peak and revers\$3 same coefficient and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:11
S65	0	model with circuit with RC and convert\$3 with discrete with time and impulse near response and deconvolut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:13
S66	1	model with circuit and convert\$3 with discrete with time and impulse near response and deconvolut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:21
S67	4	model\$3 with circuit and convert\$3 with discrete with time and impulse near response and deconvolut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:23
S68	14	non near vibrat\$4 with contact with potential with difference with sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:26
S69	8	non near vibrat\$4 with contact with potential with difference with sensor and defect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:26
S70	5	signal with wavelet with domain and coefficient and peak and backward and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:50

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S71	28	signal with wavelet with domain and coefficient and peak and (transpos\$3 invert\$3) and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 15:01
S72	0	signal with wavelet with domain and coefficient and peak and (transpos\$3 invert\$3) same coefficient and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:50
S73	8	signal with wavelet with domain and coefficient and peak and (revers\$3) same coefficient and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 15:02
S74	4	"631469".ap.	US-PGPUB; USPAT	OR	OFF	2005/09/27 15:40
S75	16	non near vibrat\$4 with potential with difference with sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/04 16:18
S76	3	non near vibrat\$4 with potential with difference with sensor and chuck	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/03 13:44
S77	2	"6011404".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/04 16:18
S78	1	702/35.ccls. and non near vibrat\$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
S79	1	702/36.ccls. and non near vibrat\$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
S80	1	438/12.ccls. and non near vibrat\$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
S81	1	134/1.3.ccls. and non near vibrat\$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
S82	6	(non near vibrat\$4 with probe with potential).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23

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S83	9	(non near vibrat\$4 with difference with potential).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23
S84	7	(non near vibrat\$4 with difference with potential and chemical).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23
S85	2	(non near vibrat\$4 with difference with potential and chemical and sample).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/10 10:45
S86	2	(non near vibrat\$4 with difference with potential and chemical and sample).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/10 11:08
S87	2	(non near vibrat\$4 with difference with potential and chemical and sample).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/09/12 08:39
S88	105	walling.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/10 11:08
S89	20	non near vibrat\$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:33
S90	3	non near vibrat\$3 with contact with potential with difference and RC	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:21
S91	3	model\$4 with RC with circuit and discrete near time near transfer near function and impulse near response and deconvolut\$3 and time near delay	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:23
S92	3	model\$4 with RC with circuit and transfer near function and impulse near response and deconvolut\$3 and time near delay	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:32
S93	1	(model\$4 with RC with circuit and transfer near function and impulse near response and deconvolut\$3 and time near delay).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:33
S94	8	(non near vibrat\$3 with contact with potential with difference).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:33

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S95	4	(non near vibrat\$3 with contact with potential with difference with pattern).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:33
S96	4	(non near vibrat\$3 with contact with potential with difference with pattern with defect).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/01/03 15:34
S97	1	steele.inv. and walling.xa.	US-PGPUB; USPAT	OR	OFF	2006/01/19 12:12
S98	2202	steele.inv.	US-PGPUB; USPAT	OR	OFF	2006/01/19 12:12
S99	0	(steele and hawthorn).inv.	US-PGPUB; USPAT	OR	OFF	2006/01/19 12:12
S100	7	(steele and hawthorne).inv.	US-PGPUB; USPAT	OR	OFF	2006/01/19 12:12
S101	554	contact near potential near difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:35
S102	84	S101 and sample with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:35
S103	4	S101 with absolute and sample with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:37
S104	4	S101 with absolute and sample with surface and vibrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:37
S105	3	S101 with absolute and sample with surface and vibrat\$3 with S101	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:37
S106	1	S101 with absolute and sample with surface and vibrat\$3 with S101 with non	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:37
S107	0	S101 with absolute and sample with surface and vibrat\$3 with S101 with without	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:39
S108	6	(rotat\$3 rotatable rotatably) with (semiconductor wafer) with stage and vibrat\$3 with contact with potential with difference and point	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:40

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S10 9	6	(rotat\$3 rotatable rotatably) with (semiconductor wafer) with stage and non with vibrat\$3 with contact with potential with difference and point	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:43
S11 0	1	((rotat\$3 rotatable rotatably) with (semiconductor wafer) with stage and non with vibrat\$3 with contact with potential with difference and point).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:41
S11 1	1	(rotat\$3 rotatable rotatably) with (semiconductor wafer) with stage and non with vibrat\$3 with contact with potential with difference and point and absolute.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 13:43
S11 2	3	(rotat\$3 rotatable rotatably) with (semiconductor wafer) with stage and non with vibrat\$3 with contact with potential with difference and point and point.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 14:24
S11 3	2	"5546477".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 14:25
S11 4	1	(absolute with S101).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 14:26
S11 5	4	(scan\$4 with non near vibrat\$3 with S101).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 14:26
S11 6	0	(scan\$4 with non near vibrat\$3 with S101 with point).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 15:24
S11 7	0	(scan\$4 with S101 near point).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 15:24
S11 8	0	(scan\$4 with S101 with point).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 15:24
S11 9	0	(scan\$4 with S101 with point).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 15:24

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S12 0	0	(scan\$4 with contact near potential near difference with point).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/13 15:24
S12 1	16	(steele and hawthorne).inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:57
S12 2	0	(steele and hawthorne).inv. and (pattern with tip).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:41
S12 3	18	contact near potential near difference near sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:58
S12 4	12	contact near potential near difference near sensor and pattern with defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:58
S12 5	12	potential near difference near sensor and pattern with defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:58
S12 6	76	potential near difference with contact and pattern with defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:00
S12 7	13	contact near potential near difference and pattern with defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:59
S12 8	21	potential near difference with contact and pattern with defect and (scan scanning)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:06
S12 9	12	potential near difference with sensor and pattern with defect and (scan scanning)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:07
S13 0	5	(potential near difference with sensor and pattern with defect and (scan scanning)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:07